

RAYCONN ELECTRONICS CO., LTD.

SPECIFICATION FORM

FEATURES

- ✧ 0.56 INCHES (14.20MM) DIGIT HEIGHT
- ✧ 50.30MM×19.0MM OUTLINE
- ✧ FOUR DIGIT
- ✧ SINGLE COLOR
- ✧ EASY ASSEMBLY
- ✧ HIGH BRIGHTNESS
- ✧ SOLID STATE RELIABILITY

DESCRIPTION

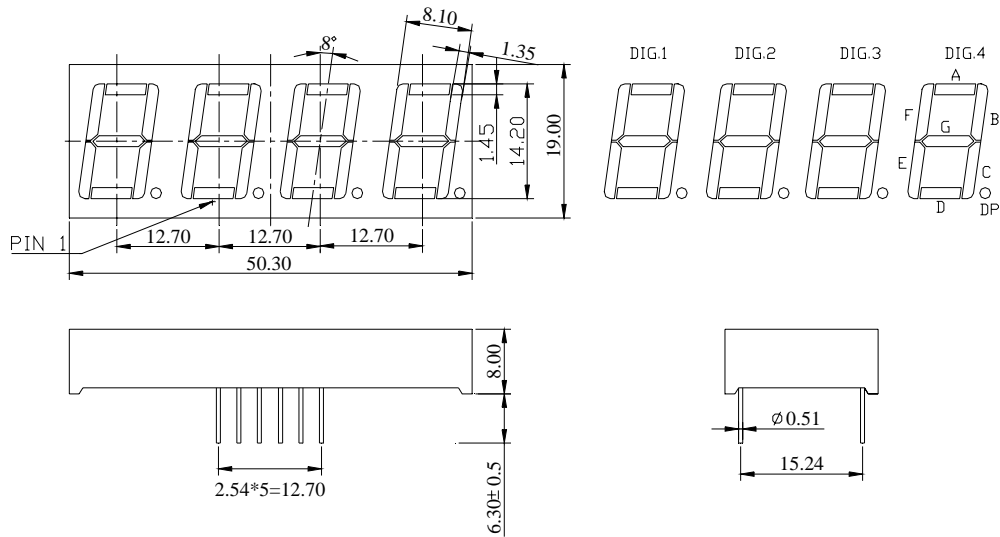
The REC-S5461CSR is a 0.56 inches(14.20mm) digit height, 50.30mm×19.0mm outline, single color, four digit and common cathode numeric display. This display utilizes super-red LED chips fabricated from GaAlAs epiwafer on GaAs substrate grown by liquid phase epitaxy. These devices have black face and white segments.

DEVICE

| PART NO. | EMITTING COLOR | DESCRIPTION |
|--------------|----------------|-----------------------------|
| REC-S5461CSR | Super-Red | Black Face & White Segments |

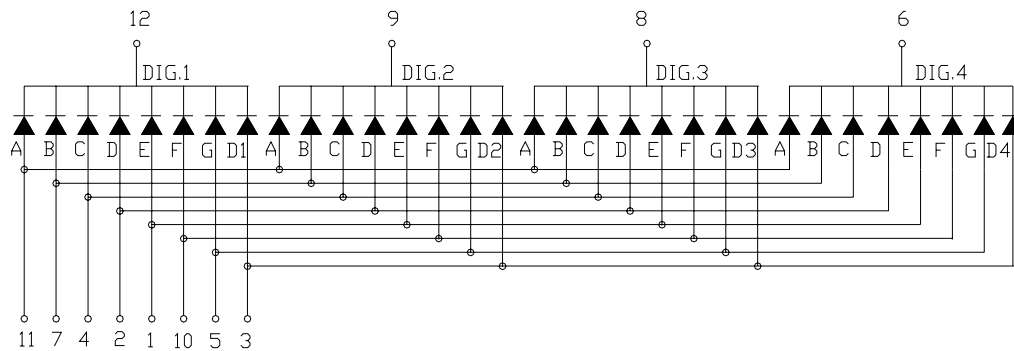
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PACKAGE DIMENSION



Note: Tolerance is ± 0.25 mm unless otherwise noted.

INTERNAL CIRCUIT DIAGRAM



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PIN CONNECTION

| PIN NO. | CONNECTION | PIN NO. | CONNECTION |
|---------|----------------------|---------|----------------------|
| 1 | Anode E | 7 | Anode B |
| 2 | Anode D | 8 | Common Cathode Dig.3 |
| 3 | Anode DP | 9 | Common Cathode Dig.2 |
| 4 | Anode C | 10 | Anode F |
| 5 | Anode G | 11 | Anode A |
| 6 | Common Cathode Dig.4 | 12 | Common Cathode Dig.1 |

ABSOLUTE MAXIMUM RATING AT $T_A=25^\circ\text{C}$

| PARAMETER | SYMBOL | MAXIMUM | UNIT |
|--|----------|--------------------|------|
| Power Dissipation per Seg. | P_{AD} | 60 | mW |
| Peak Forward Current per Seg. | I_{PF} | 80 | mA |
| Continuous Forward Current per Seg. | I_{AF} | 20 | mA |
| Reverse Voltage per Seg. | V_R | 5 | V |
| Operating Temperature Range, T_{opr} | | - 25° C to + 60° C | |
| Storage Temperature Range, T_{stg} | | - 30° C to + 85° C | |
| Solder Temperature : 1 / 16 inch below seating plane for 3 seconds at 260° C | | | |

ELECTRO - OPTICAL CHARACTERISTICS AT $T_A=25^\circ\text{C}$

| PARAMETER | UNIT | MIN | TYPE | MAX |
|--|---------------|-----|------|-----|
| Luminous Intensity per Seg., I_V ($I_F=20\text{mA}$) | mcd | 7 | 10 | 14 |
| Peak Emission Wavelength, λ_p ($I_F=20\text{mA}$) | nm | | 640 | |
| Special Line Half-Width, $\Delta\lambda$ ($I_F=20\text{mA}$) | nm | | 20 | |
| Forward Voltage per Seg., V_F ($I_F=20\text{mA}$) | V | 1.6 | 1.8 | 2.1 |
| Reverse Current per chipSeg., I_R , ($V_R=5\text{V}$) | μA | | | 100 |
| Luminous Intensity Matching Ratio, I_{V-m} ($I_F=20\text{mA}$) | | | | 2:1 |